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4.5V Drive Nch MOSFET

RMW180N03

Structure

Silicon N-channel MOSFET

Features

- 1) High Power package(PSOP8).
- 2) High-speed switching,Low On-resistance.
- 3) Low voltage drive(4.5V drive).

Application

Switching

Packaging specifications

	Package	Taping	
Type	Code	TB	
	Basic ordering unit (pieces)	2500	
RMW180N	0		

● Absolute maximum ratings (Ta = 25°C)

Parame	Symbol Limits		Unit	
Drain-source voltage		V_{DSS}	30	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	Continuous	I_D	±18	Α
	Pulsed	I _{DP} *1	±72	Α
Source current	Continuous	I _S	2.5	Α
(Body Diode)	Pulsed	I _{SP} *1	72	Α
Power dissipation		P _D *2	3.0	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

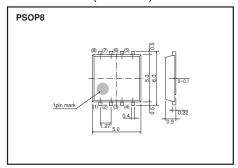
^{*1} Pw \leq 10 μ s, Duty cycle \leq 1%

Thermal resistance

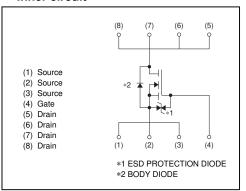
Parameter	Symbol	Limits	Unit
Channel to Ambient	Rth (ch-a)*	41.7	°C / W

^{*} MOUNTED ON 40mm × 40mm Cu BOARD

• Dimensions (Unit : mm)



• Inner circuit



^{*2} MOUNTED ON 40mm × 40mm Cu BOARD

● Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	-	-	±10	μ A	$V_{GS}=\pm20V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	30	-	-	٧	$I_D=1$ mA, $V_{GS}=0$ V
Zero gate voltage drain current	I _{DSS}	1	-	1	μ A	V_{DS} =30V, V_{GS} =0V
Gate threshold voltage	V _{GS (th)}	1.0	-	2.5	٧	$V_{DS}=10V$, $I_{D}=1mA$
Static drain-source on-state	R _{DS (on)} *	1	4.0	5.6	mΩ	$I_{D}=18A, V_{GS}=10V$
resistance	TDS (on)	1	5.5	7.7		$I_D = 18A, V_{GS} = 4.5V$
Forward transfer admittance	IY _{fs} f	15	-	-	S	$I_{D}=18A, V_{DS}=10V$
Input capacitance	C _{iss}	1	1250	-	pF	V _{DS} =15V
Output capacitance	C _{oss}	1	400	-	pF	V _{GS} =0V
Reverse transfer capacitance	C_{rss}	1	145	-	рF	f=1MHz
Turn-on delay time	t _{d(on)} *	-	14	-	ns	I _D =9A, V _{DD} ≒ 15V
Rise time	t _r *	1	39	1	ns	V _{GS} =10V
Turn-off delay time	t _{d(off)} *	1	39	-	ns	$R_L=1.67\Omega$
Fall time	t _f *	1	12	-	ns	$R_G=10\Omega$
Total gate charge	Q _g *	-	24	-	nC	I _D =18A, V _{DD} ≒15V
Gate-source charge	Q _{gs} *	-	4.4	-	nC	V _{GS} =10V
Gate-drain charge	Q _{gd} *	-	4.7	-	nC	

^{*}Pulsed

●Body diode characteristics (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward Voltage	V _{SD} *	-	-	1.2	V	I _s =2.5A, V _{GS} =0V

^{*}Pulsed

●Electrical characteristic curves (Ta=25°C)

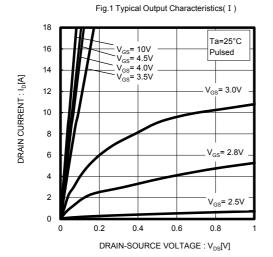
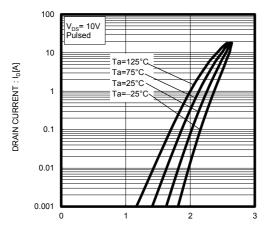


Fig.3 Typical Transfer Characteristics



 $\mathsf{GATE}\text{-}\mathsf{SOURCE}\;\mathsf{VOLTAGE}:\mathsf{V}_{\mathsf{GS}}[\mathsf{V}]$

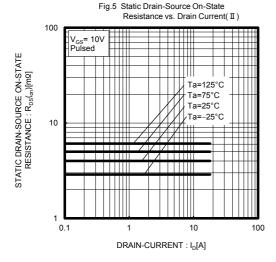


Fig.2 Typical Output Characteristics(II)

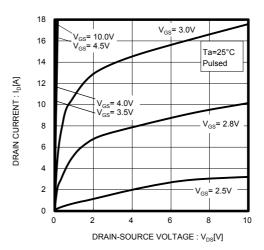


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current(I)

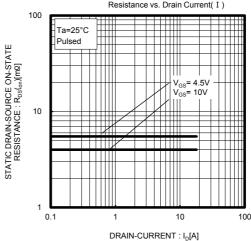
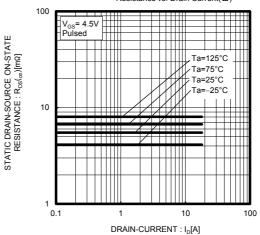
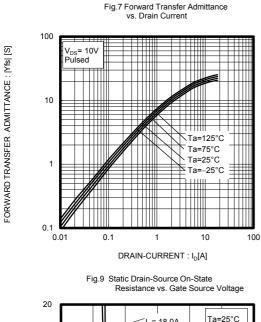
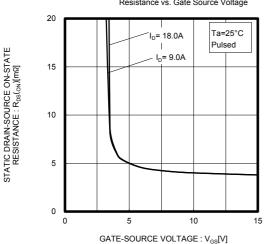
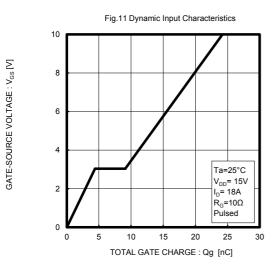


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(Ⅲ)









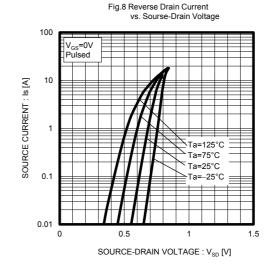
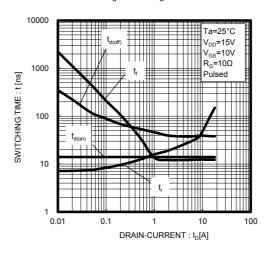


Fig.10 Switching Characteristics



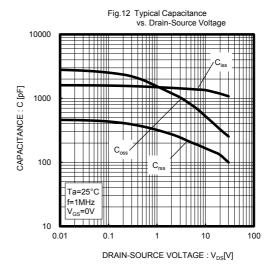


Fig.13 Maximum Safe Operating Aera

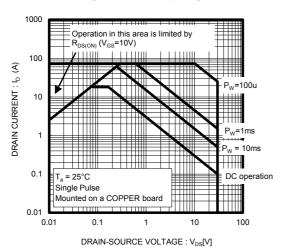
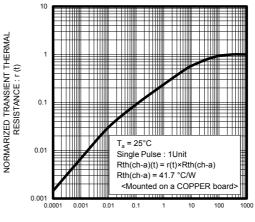


Fig.14 Normalized Transient Thermal Resistance vs. Pulse Width



Measurement circuits

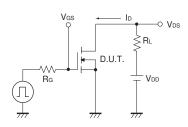


Fig.1-1 Switching Time Measurement Circuit

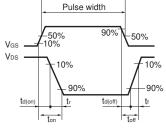
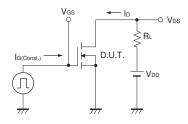


Fig.1-2 Switching Waveforms





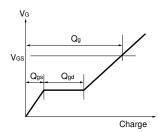


Fig.2-2 Gate Charge Waveform

Notice

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